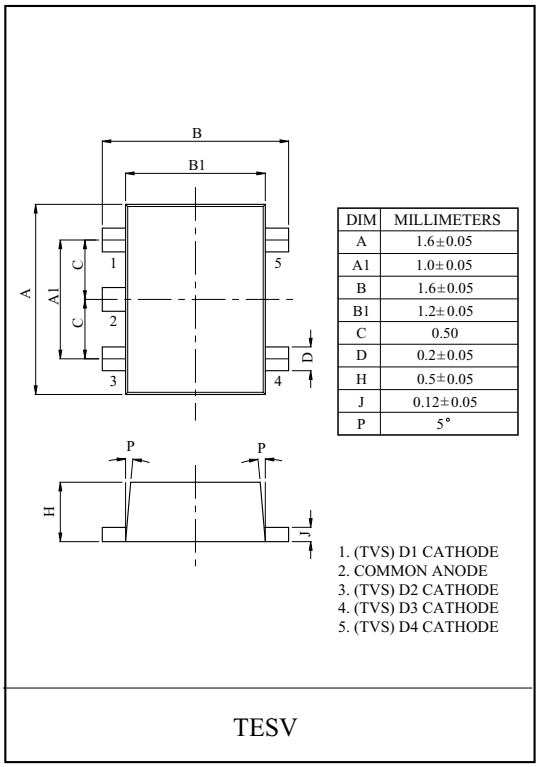
PG03DXTEV

TVS Diode Array for ESD Protection in Portable Electronics

Protection in Portable Electronics Applications.



DIM	MILLIMETERS
A	1.6±0.05
A1	1.0±0.05
B	1.6±0.05
B1	1.2±0.05
C	0.50
D	0.2±0.05
H	0.5±0.05
J	0.12±0.05
P	5°

1. (TVS) D1 CATHODE
2. COMMON ANODE
3. (TVS) D2 CATHODE
4. (TVS) D3 CATHODE
5. (TVS) D4 CATHODE

TESV

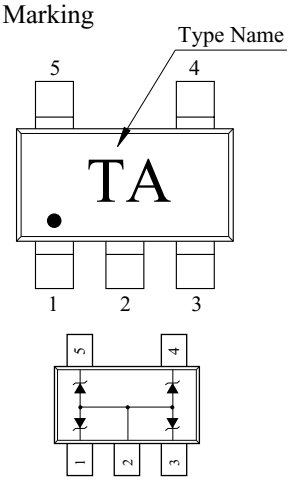
FEATURES

- ESD Protection: IEC 61000-4-2 Level 4.
  MILSTD883C-Method 3015-6:Class 3
- Four separate unidirectional configurations for protection
- Low leakage current<1μA @3Volts
- Low capacitance
- Complies to USB 1.1 low speed & high speed specifications

APPLICATIONS

- Cell phone handsets and accessories.
- Cordless phones.
- Personal digital assistants (PDA s)
- Notebooks, desktopsPC, & servers.
- Portable instrumentation.
- Set-Top Box, DVD Player.
- Digital Camera.

Marking



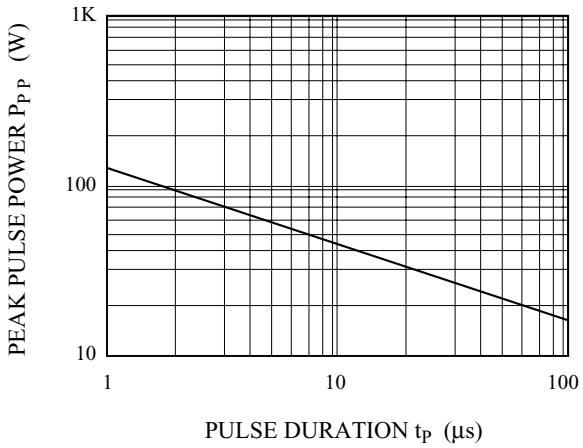
MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Peak Pulse Power (tp=8/20μs)	P_{PK}	20	W
Peak Pulse Current (tp=8/20μs)	I_{PP}	1.6	A
Operating Temperature	T_j	-55～150	℃
Storage Temperature	T_{stg}	-55～150	℃

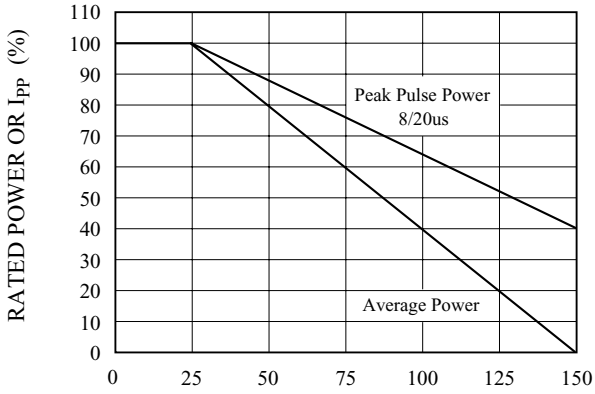
ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Reverse Stand-Off Voltage	V_{RWM}	-	-	-	3.3	V
Reverse Breakdown Voltage	V_{BR}	I_t=1mA	5.3	-	5.9	V
Reverse Leakage Current	I_R	V_{RWM}=3V	-	-	1	μA
Clamping Voltage	V_C	I_{PP}=1.6A, tp=8/20μs	-	-	13	V
Junction Capacitance	C_J	V_R=0V, f=1MHz	-	13	17	pF
		V_R=3.0V, f=1MHz	-	7.0	11.5	

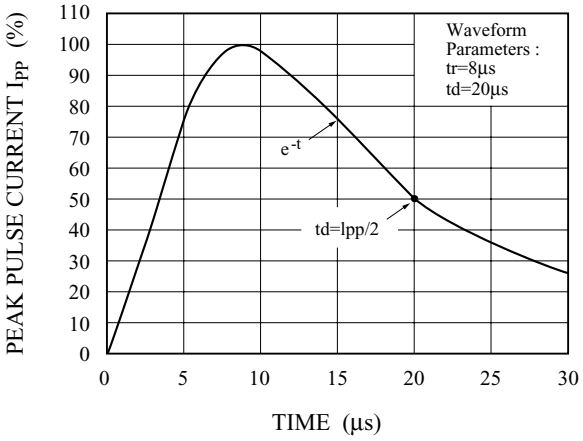
NON-REPETITIVE PEAK PULSE POWER VS. PULSE TIME



POWER DERATION CURVE



PULSE WAVEFORM



C_J - V_R

